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1.5 Ω On Resistance, ±15 V/12 V/±5 V, *i*CMOS, Dual SPDT Switch

Data Sheet ADG1436

FEATURES

1.5 Ω on resistance
0.3 Ω on-resistance flatness
0.1 Ω on-resistance match between channels
Continuous current per channel
LFCSP package: up to 400 mA
TSSOP package: up to 260 mA
Fully specified at +12 V, ±15 V, and ±5 V
No V_L supply required
3 V logic-compatible inputs

16-lead TSSOP and 4 mm × 4 mm, 16-lead LFCSP packages

APPLICATIONS

Rail-to-rail operation

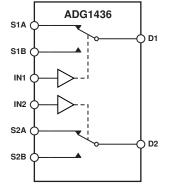
Automatic test equipment
Data acquisition systems
Battery-powered systems
Sample-and-hold systems
Audio signal routing
Communication systems
Relay replacement

GENERAL DESCRIPTION

The ADG1436 is a monolithic CMOS device containing two independently selectable SPDT switches. An EN input on the LFCSP package enables or disable the device. When disabled, all channels are switched off. Each switch conducts equally well in both directions when on and has an input signal range that extends to the supplies. In the off condition, signal levels up to the supplies are blocked. Both switches exhibit break-beforemake switching action for use in multiplexer applications.

The ADG1436 is designed on an *i*CMOS° process. *i*CMOS (industrial-CMOS) is a modular manufacturing process combining high voltage CMOS (complementary metal-oxide semiconductor) and bipolar technologies. It enables the development of a wide range of high performance analog ICs capable of 33 V operation in a footprint that no previous generation of high voltage parts has been able to achieve. Unlike analog ICs using conventional

FUNCTIONAL BLOCK DIAGRAMS



SWITCHES SHOWN FOR A ONE-INPUT LOGIC. §

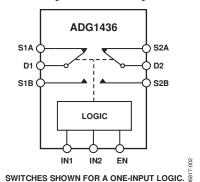


Figure 2. LFCSP Package

CMOS processes, *i*CMOS components can tolerate high supply voltages while providing increased performance, dramatically lower power consumption, and reduced package size.

The on-resistance profile is very flat over the full analog input range, ensuring excellent linearity and low distortion when switching audio signals. *i*CMOS construction ensures ultralow power dissipation, making the part ideally suited for portable and battery-powered instruments.

PRODUCT HIGHLIGHTS

- 1. 2.6Ω maximum on resistance over temperature.
- 2. Minimum distortion.
- 3. Ultralow power dissipation: $<0.03 \mu W$.
- 4. 16-lead TSSOP and 16-lead 4 mm × 4 mm LFCSP packages.

ADG1436* PRODUCT PAGE QUICK LINKS

Last Content Update: 02/23/2017

COMPARABLE PARTS 🖵

View a parametric search of comparable parts.

EVALUATION KITS

 Evaluation Board for 16 lead TSSOP Devices in the Switch/ Mux Portfolio

DOCUMENTATION

Application Notes

 AN-1024: How to Calculate the Settling Time and Sampling Rate of a Multiplexer

Data Sheet

 ADG1436: 1.5 Ω On Resistance, ±15 V/12 V/±5 V, iCMOS, Dual SPDT Switch Data Sheet

User Guides

 UG-945: Evaluation Board for 16-Lead TSSOP Devices in the Switches and Multiplexers Portfolio

REFERENCE MATERIALS \Box

Informational

• iCMOS Technology Enabling the +/-10V World

Product Selection Guide

· Switches and Multiplexers Product Selection Guide

DESIGN RESOURCES 🖵

- · ADG1436 Material Declaration
- PCN-PDN Information
- · Quality And Reliability
- Symbols and Footprints

DISCUSSIONS

View all ADG1436 EngineerZone Discussions.

SAMPLE AND BUY 🖳

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TECHNICAL SUPPORT

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DOCUMENT FEEDBACK \Box

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Updated Outline Dimensions
Changes to Ordering Guide
3/2009—Rev. 0 to Rev. A
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SPECIFICATIONS

15 V DUAL SUPPLY

 V_{DD} = 15 V \pm 10%, V_{SS} = –15 V \pm 10%, GND = 0 V, unless otherwise noted.

Table 1.

Parameter	25°C	-40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			V _{DD} to V _{SS}	V	
On Resistance (R _{ON})	1.5			Ωtyp	$V_S = \pm 10 \text{ V}, I_S = -10 \text{ mA}; \text{ see Figure 23}$
(10.1)	1.8	2.3	2.6	Ω max	$V_{DD} = +13.5 \text{ V}, V_{SS} = -13.5 \text{ V}$
On-Resistance Match	0.1	2.3	2.0	Ωtyp	$V_S = \pm 10 \text{ V. } I_S = -10 \text{ mA}$
Between Channels (ΔR _{ON})	0.1			12 (yp	V3-110 V, IS- 10 IIIA
	0.18	0.19	0.21	Ω max	
On-Resistance Flatness (R _{FLAT(ON)})	0.28			Ωtyp	$V_S = \pm 10 \text{ V, } I_S = -10 \text{ mA}$
OTT TO STATE OF THE STATE OF TH	0.36	0.4	0.45	Ω max	13 210 1/13 10 11
EAKAGE CURRENTS	0.50		01.15	22111071	$V_{DD} = +16.5 \text{ V}, V_{SS} = -16.5 \text{ V}$
Source Off Leakage, Is (Off)	±0.04			nA typ	$V_S = \pm 10 \text{ V}, V_S = \pm 10 \text{ V}; \text{ see Figure 24}$
Source on Leakage, is (Oil)	±0.55	±2	±12.5	nA max	vs = ±10 v, vs = ±10 v, see Figure 24
Drain Off Leakage, I _D (Off)	±0.04	12	112.5	_	$V_S = \pm 10 \text{ V}, V_S = \pm 10 \text{ V}; \text{ see Figure 24}$
Drain On Leakage, ib (On)			.12.5	nA typ	$v_s = \pm 10 \text{ v}, v_s = \pm 10 \text{ v}; \text{ see Figure 24}$
	±0.55	±2	±12.5	nA max	V V 110V 5: 25
Channel On Leakage, I_D , I_S (On)	±0.1		. 25	nA typ	$V_S = V_D = \pm 10 \text{ V}$; see Figure 25
DIGITAL INDUITS	±2	±4	±35	nA max	
DIGITAL INPUTS					
Input High Voltage, V _{INH}			2.0	V min	
Input Low Voltage, V _{INL}			0.8	V max	
Input Current, I _{INL} or I _{INH}	0.005			μA typ	$V_{IN} = V_{GND}$ or V_{DD}
			±0.1	μA max	
Digital Input Capacitance, C _{IN}	3.5			pF typ	
DYNAMIC CHARACTERISTICS ¹					
Transition Time, t _{TRANSITION}	125			ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
	170	215	245	ns max	$V_S = +10 \text{ V}$; see Figure 30
t _{on} (EN)	95			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	120	140	155	ns max	V _s = 10 V; see Figure 30
toff (EN)	105			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	130	150	170	ns max	V _s = 10 V; see Figure 30
Break-Before-Make Time Delay, t _{BBM}	20			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
,, . <u></u>			10	ns min	$V_{S1} = V_{S2} = +10 \text{ V}; \text{ see Figure 31}$
Charge Injection	-20			pC typ	$V_S = 0 \text{ V}, R_S = 0 \Omega, C_L = 1 \text{ nF}; \text{ see Figure 33}$
Off Isolation	-80			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$; see Figure 26
Channel-to-Channel Crosstalk	-80			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$; see Figure 27
Total Harmonic Distortion + Noise	0.011			% typ	$R_L = 110 \Omega$, 15 V p-p, f = 20 Hz to 20 kHz; see
Total Harmonic Distortion 1 Noise	0.011			70 typ	Figure 29
-3 dB Bandwidth	110			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 28
Insertion Loss	-0.18			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 28
C _s (Off)	23			pF typ	f = 1 MHz, V _s = 0 V
C _D (Off)	50			pF typ	$f = 1 \text{ MHz}, V_S = 0 \text{ V}$
C _D , C _S (On)	120			pF typ	$f = 1 \text{ MHz}, V_S = 0 \text{ V}$ $f = 1 \text{ MHz}, V_S = 0 \text{ V}$
	120			рг тур	$V_{DD} = +16.5 \text{ V}, V_{SS} = -16.5 \text{ V}$
POWER REQUIREMENTS	0.001			4	
I_{DD}	0.001			μA typ	Digital Inputs = 0 V or V _{DD}
	1		1	μA max	S
IDD	170			μA typ	Digital Input = 5 V
	1		285	μA max	
Iss	0.001			μA typ	Digital Inputs = 0 V , 5 V , or V_{DD}
	1		1.0	μA max	
V_{DD}/V_{SS}	1	1	±4.5/±16.5	V min/max	GND = 0 V

 $^{^{\}rm 1}\,\mbox{Guaranteed}$ by design, not subject to production test.

12 V SINGLE SUPPLY

 V_{DD} = 12 V ± 10%, V_{SS} = 0 V, GND = 0 V, unless otherwise noted.

Table 2.

Parameter	25°C	-40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			0 V to V _{DD}	V	
On Resistance (R _{ON})	2.8			Ωtyp	$V_s = 0 \text{ V to } 10 \text{ V}, I_s = -10 \text{ mA}; \text{ see Figure 23}$
, ,	3.5	4.3	4.8	Ω max	$V_{DD} = +10.8 \text{ V}, V_{SS} = 0 \text{ V}$
On-Resistance Match	0.13			Ωtyp	$V_S = 0 \text{ V to } 10 \text{ V}, I_S = -10 \text{ mA}$
Between Channels (ΔR _{ON})	0.21	0.22	0.25	0	
On Business Flateres (B.	0.21	0.23	0.25	Ω max	V 0V4 10V4 10 40
On-Resistance Flatness (R _{FLAT(ON)})	0.6	4.3	4.2	Ωtyp	$V_S = 0 \text{ V to } 10 \text{ V}, I_S = -10 \text{ mA}$
LEAVAGE GUDDENITG	1.1	1.2	1.3	Ω max	
LEAKAGE CURRENTS					$V_{DD} = 13.2 \text{ V}, V_{SS} = 0 \text{ V}$
Source Off Leakage, I₅ (Off)	±0.04			nA typ	$V_S = 1 \text{ V/}10 \text{ V}, V_D = 10 \text{ V/}1 \text{ V}; \text{ see Figure 24}$
	±0.55	±2	±12.5	nA max	
Drain Off Leakage, I _D (Off)	±0.04			nA typ	$V_S = 1 \text{ V}/10 \text{ V}, V_D = 10 \text{ V}/1 \text{ V}; \text{ see Figure 24}$
	±0.55	±2	±12.5	nA max	
Channel On Leakage, ID, IS (On)	±0.1			nA typ	$V_S = V_D = 1 \text{ V or } 10 \text{ V}$; see Figure 25
	±1	±4	±35	nA max	
DIGITAL INPUTS					
Input High Voltage, V _{INH}			2.0	V min	
Input Low Voltage, V _{INL}			0.8	V max	
Input Current, I _{INL} or I _{INH}	0.001			μA typ	$V_{IN} = V_{GND}$ or V_{DD}
,			±0.1	μA max	
Digital Input Capacitance, C _{IN}	3.5			pF typ	
DYNAMIC CHARACTERISTICS ¹	5.5			P. 1)P	
Transition Time, transition	200			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
Transition Time, transition	270	320	350	ns max	$V_s = 8 \text{ V}$; see Figure 30
+ (EN)	175	320	330		$R_L = 300 \Omega$, $C_L = 35 pF$
t _{on} (EN)	235	280	310	ns typ	•
+ (FNI)		280	310	ns max	$V_s = 8 \text{ V}$; see Figure 30
t _{OFF} (EN)	105	175	105	ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
Dood Bofon Male Ton Dale 1	145	175	195	ns max	$V_s = 8 \text{ V}$; see Figure 30
Break-Before-Make Time Delay, t _{BBM}	70			ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
			10	ns min	$V_{S1} = V_{S2} = 8 \text{ V}$; see Figure 31
Charge Injection	30			pC typ	$V_S = 6 \text{ V}, R_S = 0 \Omega, C_L = 1 \text{ nF}; \text{ see Figure 33}$
Off Isolation	-80			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$; see Figure 26;
Channel-to-Channel Crosstalk	-80			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$; see Figure 27
−3 dB Bandwidth	78			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 28
Insertion Loss	-0.3			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 28
C _s (Off)	40			pF typ	f = 1 MHz, V _s = 6 V
C _D (Off)	80			pF typ	$f = 1 \text{ MHz}, V_S = 6 \text{ V}$
C _D , C _S (On)	140			pF typ	$f = 1 \text{ MHz}, V_S = 6 \text{ V}$
POWER REQUIREMENTS	1.0			F7P	$V_{DD} = 13.2 \text{ V}$
	0.001			μA typ	Digital inputs = 0 V or V_{DD}
IDD	0.001		1.0	μΑ τyp μΑ max	Digital inputs – 0 v of voo
L.	170		1.0		Digital inputs – 5 V
I_{DD}	170		205	μA typ	Digital inputs = 5 V
V			285	μA max	CND OVV OV
V_{DD}			5/16.5	V min/max	$GND = 0 V, V_{SS} = 0 V$

 $^{^{\}mbox{\tiny 1}}$ Guaranteed by design, not subject to production test.

5 V DUAL SUPPLY

 V_{DD} = 5 V \pm 10%, V_{SS} = –5 V \pm 10%, GND = 0 V, unless otherwise noted.

Table 3.

Parameter	25°C	-40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			V _{DD} to V _{SS}	V	
On Resistance (R _{ON})	3.3			Ωtyp	$V_s = \pm 4.5 \text{ V, } I_s = -10 \text{ mA; see Figure 23}$
	4	4.9	5.4	Ω max	$V_{DD} = +4.5 \text{ V}, V_{SS} = -4.5 \text{ V}$
On-Resistance Match	0.13			Ωtyp	$V_S = \pm 4.5 \text{ V}, I_S = -10 \text{ mA}$
Between Channels (ΔR _{ON})				>	13 2 10 17 13
	0.22	0.23	0.25	Ω max	
On-Resistance Flatness (R _{FLAT(ON)})	0.9			Ωtyp	$V_s = \pm 4.5 \text{ V. } I_s = -10 \text{ mA}$
(.2.(,	1.1	1.24	1.31	Ω max	,
LEAKAGE CURRENTS					$V_{DD} = +5.5 \text{ V}, V_{SS} = -5.5 \text{ V}$
Source Off Leakage, Is (Off)	±0.03			nA typ	·
Source on Leanage, is (on)					$V_S = \pm 4.5 \text{ V}, V_D = \mp 4.5 \text{ V}; \text{ see Figure 24}$
	±0.2	±1	±12.5	nA max	
Drain Off Leakage, I _D (Off)	±0.03			nA typ	$V_{S} = \pm 4.5 \text{ V}, V_{D} = \mp 4.5 \text{ V}; \text{ see Figure 24}$
	±0.2	±1	±12.5	nA max	
Channel On Leakage, ID, Is (On)	±0.05			nA typ	$V_S = V_D = \pm 4.5V$; see Figure 25
5	±0.25	±1.5	±35	nA max	
DIGITAL INPUTS					
Input High Voltage, V _{INH}			2.0	V min	
Input Low Voltage, V _{INL}			0.8	V max	
Input Current, I _{INL} or I _{INH}	0.001		0.0	μA typ	$V_{IN} = V_{GND}$ or V_{DD}
input current, int or inh	0.001		±0.1	μΑ max	VIN — VGND OI VDD
Digital Input Capacitance, C _{IN}	3.5		10.1		
DYNAMIC CHARACTERISTICS ¹	3.3			pF typ	
	210				D 200 C 25 "F
Transition Time, t _{TRANSITION}	310	510	565	ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
(5)	445	510	565	ns max	$V_s = 3 V$; see Figure 30
t _{on} (EN)	255			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	355	415	460	ns max	$V_s = 3 \text{ V}$; see Figure 30
t _{OFF} (EN)	215			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	305	355	400	ns max	$V_s = 3 \text{ V}$; see Figure 30
Break-Before-Make Time Delay, t _{BBM}	80			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
			10	ns min	$V_{S1} = V_{S2} = 3 \text{ V; see Figure 31}$
Charge Injection	30			pC typ	$V_S = 0 \text{ V}$, $R_S = 0 \Omega$, $C_L = 1 \text{ nF}$; see Figure 33
Off Isolation	-80			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$; see Figure 26
Channel-to-Channel Crosstalk	-80			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$; see Figure 27
Total Harmonic Distortion + Noise	0.03			% typ	R_L = 110 Ω, 2.5 V pp, f = 20 Hz to 20 kHz; see Figure 29
-3 dB Bandwidth	85			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 28
Insertion Loss	-0.28			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 28
C _s (Off)	33			pF typ	$V_S = 0 \text{ V, } f = 1 \text{ MHz}$
C _D (Off)	65			pF typ	$V_s = 0 V, f = 1 MHz$
C _D , C _s (On)	145			pF typ	$V_s = 0 V, f = 1 MHz$
POWER REQUIREMENTS	5			F. 7P	$V_{DD} = +5.5 \text{ V}, V_{SS} = -5.5 \text{ V}$
I _{DD}	0.001			μA typ	Digital inputs = 0 V or V_{DD}
טטו	0.001		1.0		Digital ilipats – 0 v ol vob
1	0.001		1.0	μA max	Digital inputs 01/071/
Iss	0.001		1.0	μA typ	Digital inputs = 0 V or V_{DD}
V 0/			1.0	μA max	CND OV
V_{DD}/V_{SS}			±4.5/±16.5	V min/max	GND = 0 V

¹ Guaranteed by design, not subject to production test.

CONTINUOUS CURRENT PER CHANNEL

Table 4.

Parameter	25°C	85°C	125°C	Unit	Test Conditions/Comments
CONTINUOUS CURRENT PER CHANNEL ¹					
15 V Dual Supply					$V_{DD} = +13.5 \text{ V}, V_{SS} = -13.5 \text{ V}$
ADG1436 TSSOP	260	170	100	mA max	
ADG1436 LFCSP	400	250	120	mA max	
12 V Single Supply					$V_{DD} = 10.8 \text{ V}, V_{SS} = 0 \text{ V}$
ADG1436 TSSOP	240	160	100	mA max	
ADG1436 LFCSP	350	240	120	mA max	
5 V Dual Supply					$V_{DD} = +4.5 \text{ V}, V_{SS} = -4.5 \text{ V}$
ADG1436 TSSOP	240	160	100	mA max	
ADG1436 LFCSP	300	240	120	mA max	

 $^{^{\}rm 1}\,\mbox{Guaranteed}$ by design, not subject to production test.

ABSOLUTE MAXIMUM RATINGS

 $T_A = 25$ °C, unless otherwise noted.

Table 5.

Table 5.	
Parameter	Ratings
V _{DD} to V _{SS}	35 V
V_{DD} to GND	−0.3 V to +25 V
V_{SS} to GND	+0.3 V to −25 V
Analog Inputs ¹	$V_{SS} - 0.3 \text{ V to } V_{DD} + 0.3 \text{ V or}$ 30 mA, whichever occurs first
Digital Inputs ¹	$GND - 0.3 V$ to $V_{DD} + 0.3 V$ or 30 mA, whichever occurs first
Peak Current, S or D	600 mA (pulsed at 1 ms, 10% duty cycle maximum)
Continuous Current per Channel, S or D ²	Data + 15%
Operating Temperature Range	
Automotive (Y Version)	–40°C to +125°C
Storage Temperature Range	−65°C to +150°C
Junction Temperature	150°C
16-Lead TSSOP, θ _{JA} Thermal Impedance (4-Layer Board)	112°C/W
16-Lead LFCSP, θ _{JA} Thermal Impedance	30.4°C/W
Reflow Soldering Peak Temperature, Pb Free	260(+0/-5)°C

¹ Over voltages at IN, S, and D are clamped by internal diodes. Current must be limited to the maximum ratings given.

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

² See data given in Table 4.

PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS

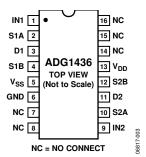
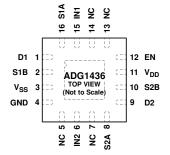


Figure 3.TSSOP Pin Configuration



NOTES
1. EXPOSED PAD TIED TO SUBSTRATE, V_{SS}.
2. NC = NO CONNECT.

Figure 4. LFCSP Pin Configuration

Table 6. Pin Function Descriptions

Pin	No.		
TSSOP	LFCSP	Mnemonic	Function
1	15	IN1	Logic Control Input.
2	16	S1A	Source Terminal. Can be an input or output.
3	1	D1	Drain Terminal. Can be an input or output.
4	2	S1B	Source Terminal. Can be an input or output.
5	3	Vss	Most Negative Power Supply Potential.
6	4	GND	Ground (0 V) Reference.
7, 8, 14 to 16	5, 7, 13, 14	NC	No Connect.
9	6	IN2	Logic Control Input.
10	8	S2A	Source Terminal. Can be an input or output.
11	9	D2	Drain Terminal. Can be an input or output.
12	10	S2B	Source Terminal. Can be an input or output.
13	11	V_{DD}	Most Positive Power Supply Potential.
N/A	12	EN	Active High Digital Input. When this pin is low, the device is disabled and all switches are off. When this pin is high, INx logic inputs determine the on switches.

TRUTH TABLE FOR SWITCHES

Table 7. ADG1436 TSSOP Truth Table

INx	SxA	SxB
0	Off	On
1	On	Off

Table 8. ADG1436 LFCSP Truth Table

EN	INx	SxA	SxB
0	X	Off	Off
1	0	Off	On
1	1	On	Off

TYPICAL PERFORMANCE CHARACTERISTICS

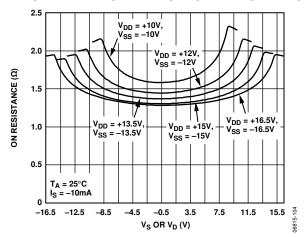


Figure 5. On Resistance vs. V_D or V_S , Dual Supply

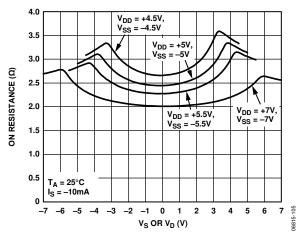


Figure 6. On Resistance vs. V_D or V_S , Dual Supply

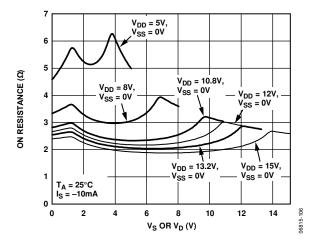


Figure 7. On Resistance vs. V_D or V_S , Single Supply

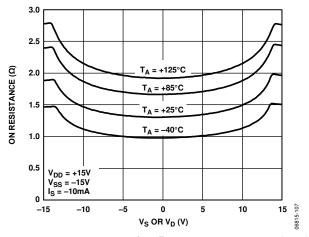


Figure 8. On Resistance vs. V_D or V_S for Different Temperatures, 15 V Dual Supply

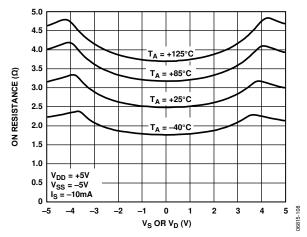


Figure 9. On Resistance vs. V_D or V_S for Different Temperatures, 5 V Dual Supply

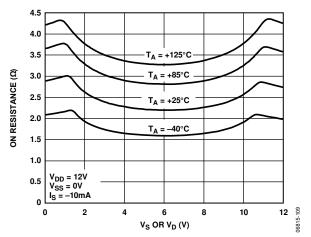


Figure 10. On Resistance vs. V_D or V_S for Different Temperatures, Single Supply

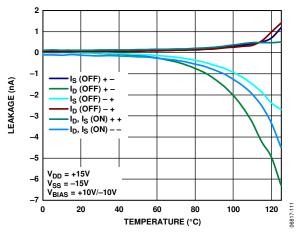


Figure 11. Leakage Currents vs. Temperature, 15 V Dual Supply

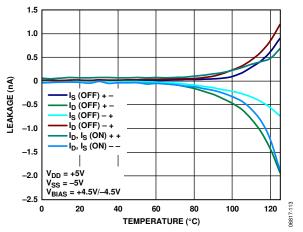


Figure 12. Leakage Currents vs. Temperature, 5 V Dual Supply

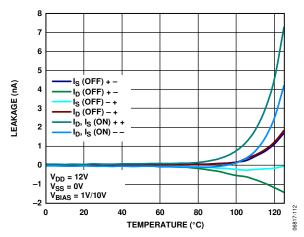


Figure 13. Leakage Currents vs. Temperature, 12 V Single Supply

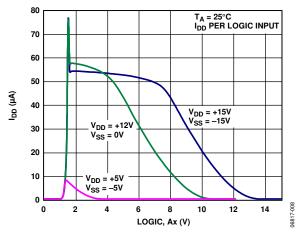


Figure 14. IDD vs. Logic Level

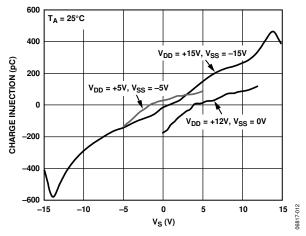


Figure 15. Charge Injection vs. Source Voltage

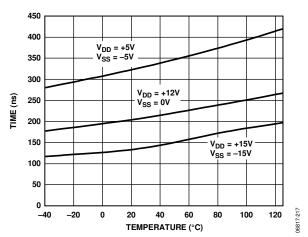


Figure 16. t_{TRANSITION} Time vs. Temperature

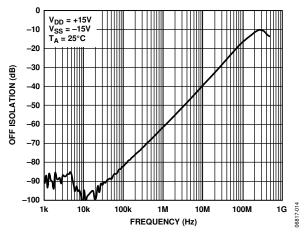


Figure 17. Off Isolation vs. Frequency

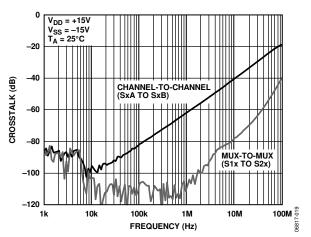


Figure 18. Crosstalk vs. Frequency

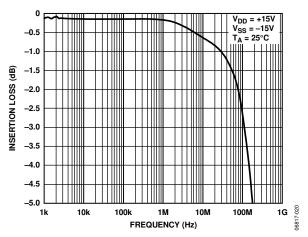


Figure 19. On Response vs. Frequency

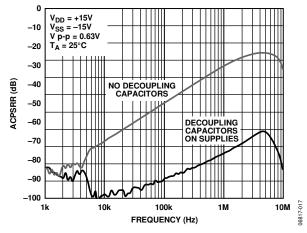


Figure 20. ACPSRR vs. Frequency

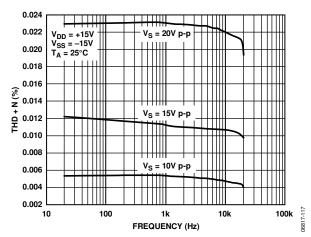


Figure 21. THD + N vs. Frequency, 15 V Dual Supply

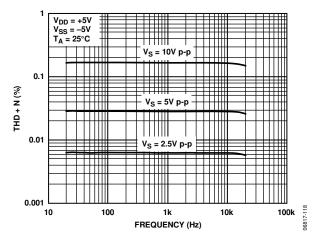


Figure 22. THD + N vs. Frequency, 5 V Dual Supply

TERMINOLOGY

 I_{DD}

The positive supply current.

 I_{ss}

The negative supply current.

 V_D, V_S

The analog voltage on Terminal D and Terminal S.

RON

The ohmic resistance between Terminal D and Terminal S.

R_{FLAT(ON)}

Flatness that is defined as the difference between the maximum and minimum value of on resistance measured over the specified analog signal range.

Is (Off)

The source leakage current with the switch off.

I_D (Off)

The drain leakage current with the switch off.

 I_D , I_S (On)

The channel leakage current with the switch on.

 \mathbf{V}_{INI}

The maximum input voltage for Logic 0.

 V_{INH}

The minimum input voltage for Logic 1.

 I_{INL} , I_{INH}

The input current of the digital input.

Cs (Off)

The off-switch source capacitance, which is measured with reference to ground.

C_D (Off)

The off-switch drain capacitance, which is measured with reference to ground.

C_D , C_S (On)

The on-switch capacitance, which is measured with reference to ground.

 C_{IN}

The digital input capacitance.

tTRANSITION

The delay time between the 50% and 90% points of the digital input and switch on condition when switching from one address state to another.

Charge Injection

A measure of the glitch impulse transferred from the digital input to the analog output during switching.

Off Isolation

A measure of unwanted signal coupling through an off switch.

Crosstalk

A measure of unwanted signal that is coupled through from one channel to another as a result of parasitic capacitance.

Bandwidth

The frequency at which the output is attenuated by 3 dB.

On Response

The frequency response of the on switch.

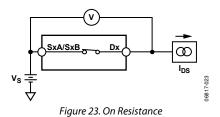
Insertion Loss

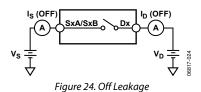
The loss due to the on resistance of the switch.

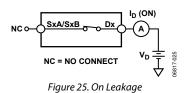
THD + N

The ratio of the harmonic amplitude plus noise of the signal to the fundamental.

TEST CIRCUITS







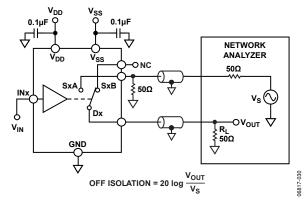


Figure 26. Off Isolation

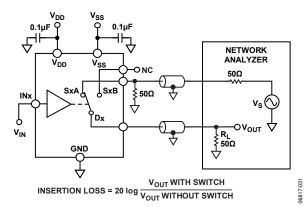


Figure 27. Channel-to-Channel Crosstalk

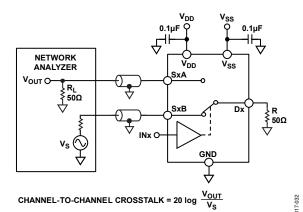


Figure 28. Bandwidth

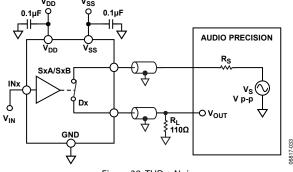


Figure 29. THD + Noise

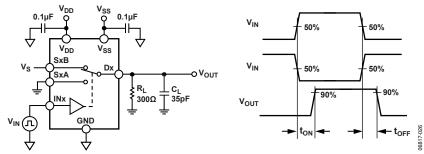


Figure 30. Switching Times

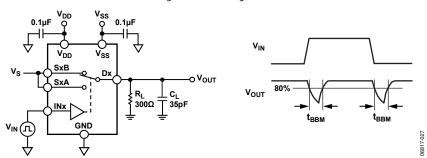
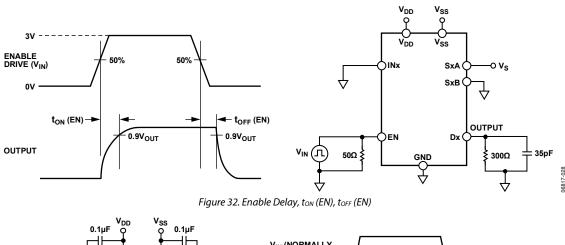


Figure 31. Break-Before-Make Time Delay



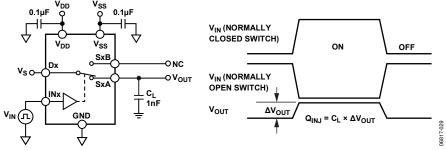
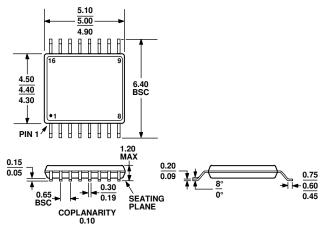


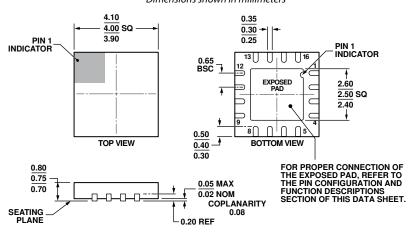
Figure 33. Charge Injection

OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MO-153-AB

Figure 34. 16-Lead Thin Shrink Small Outline Package [TSSOP] (RU-16) Dimensions shown in millimeters



COMPLIANT TO JEDEC STANDARDS MO-220-WGGC.

Figure 35. 16-Lead Lead Frame Chip Scale Package [LFCSP]

4 mm × 4 mm Body and 0.75 mm Package Height

(CP-16-26)

Dimensions shown in millimeters

ORDERING GUIDE

ONDERING COIDE							
Model ¹	Temperature Range	Package Description	Package Option				
ADG1436YRUZ	-40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16				
ADG1436YRUZ-REEL7	-40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16				
ADG1436YCPZ-REEL	-40°C to +125°C	16-Lead Lead Frame Chip Scale Package [LFCSP]	CP-16-26				
ADG1436YCPZ-REEL7	-40°C to +125°C	16-Lead Lead Frame Chip Scale Package [LFCSP]	CP-16-26				

¹ Z = RoHS Compliant Part.

